a liner comprising a compound including silicon and carbon, the liner positioned between at least a portion of the dielectric layer and a conductive element.

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2. (amended) The integrated circuit structure of Claim 1, wherein the ilner is selected from the group consisting of silicon carbide, silicon oxy-carbide, and silicon boron-carbide.

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- 11. (amended) An integrated circuit structure comprising a liner positioned between at least a portion of a dielectric layer and a conductive element, the liner comprising a compound including silicon and carbon.
- 12. (amended) The integrated circuit structure of Claim 11, wherein the liner is selected from the group consisting of silicon carbide, silicon oxy-carbide, and silicon boron-carbide.